

30V N-Channel Enhancement Mode MOSFET

Voltage 30 V Current 5.6 A

Features

- RDS(ON), VGS@10V, ID@5.6A<30mΩ
- RDS(ON) , VGS@4.5V, ID@3.5A<45mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

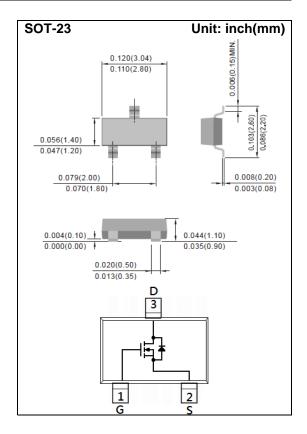
Mechanical Data

• Case: SOT-23 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0003 ounces, 0.0084 grams

Marking : A04



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V _G s	<u>+</u> 20	V
Continuous Drain Current		ID	5.6	Α
Pulsed Drain Current		I _{DM}	22	Α
Power Dissipation	T _a =25°C	D	1.25	W
	Derate above 25°C	P _D	10	mW/°C
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C
Typical Thermal Resistance				
- Junction to Ambient ^(Note 3)		Reja	100	°C/W



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250uA	1.0	1.33	2.1	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =5.6A	-	27	30	0	
		V _{GS} =4.5V, I _D =3.5A	-	39	45 mΩ		
Zero Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V	-	0.01	1	uA	
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	<u>+</u> 10	<u>+</u> 100	nA	
Dynamic							
Total Gate Charge	Q_g	\/ A5\/ 5.0A	-	7.8	-	nC	
Gate-Source Charge	Q_{gs}	V _{DS} =15V, I _D =5.6A, V _{GS} =10V ^(Note 1,2)	-	1.2	-		
Gate-Drain Charge	Q_{gd}	VGS=10V(Note 1,2)	-	1.5	-		
Input Capacitance	Ciss	\/ 45\/ \/ 0\/	-	343	-	pF	
Output Capacitance	Coss	V _{DS} =15V, V _{GS} =0V,	-	48	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	34	-		
Switching							
Turn-On Delay Time	td _(on)	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	3	-		
Turn-On Rise Time	tr	V _{DD} =15V, I _D =5.6A,	-	40	-	ns	
Turn-Off Delay Time	td _(off)	$V_{GS}=10V$, $R_{G}=3\Omega^{(Note 1,2)}$	-	38	-		
Turn-Off Fall Time	tf	RG=3\(\frac{1}{2}\)	-	39	-		
Drain-Source Diode							
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	1.5	А	
Diode Forward Voltage	V _{SD}	Is=1.0A, V _{GS} =0V	-	0.77	1.2	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.



TYPICAL CHARACTERISTIC CURVES

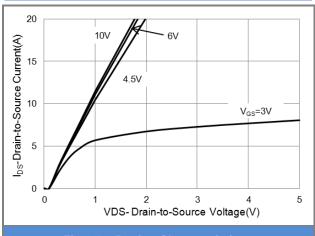


Fig.1 On-Region Characteristics

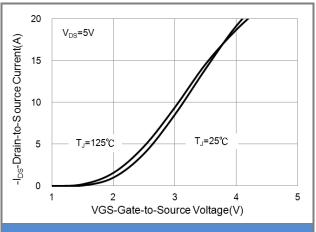


Fig.2 Transfer Characteristics

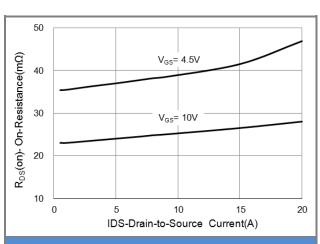


Fig.3 On-Resistance vs. Drain Current

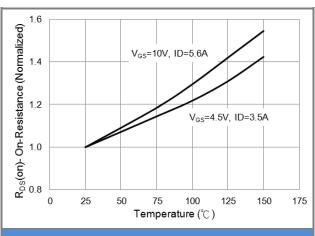
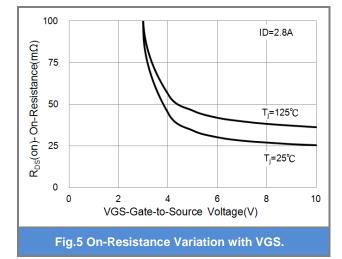
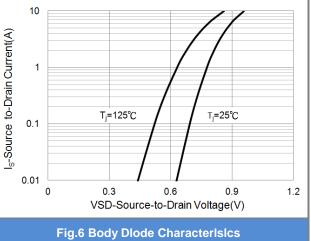


Fig.4 On-Resistance vs. Junction temperature







TYPICAL CHARACTERISTIC CURVES

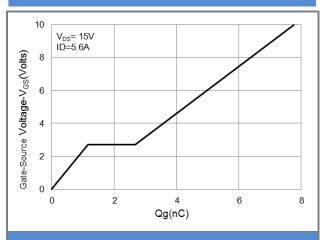


Fig.7 Gate-Charge Characteristics

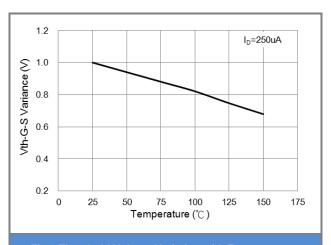


Fig.8 Threshold Voltage Variation with Temperature

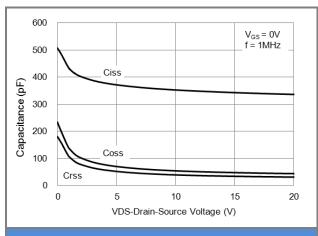


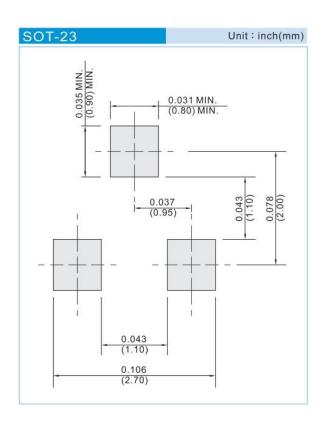
Fig.9 Capacitance vs. Drain-Source Voltage.



Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJA3404	SOT-23	3K pcs / 7" reel	A04	

Mounting Pad Layout





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DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B
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